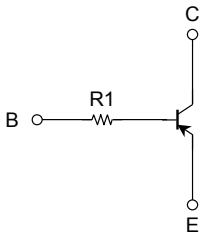
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor Built-in Transistor)

RN2912FS, RN2913FS

Switching, Inverter Circuit, Interface Circuit and
Driver Circuit Applications

- Two devices are incorporated into a fine pitch small mold (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
  Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN1912FS and RN1913FS

Equivalent Circuit and Bias Resistor Values

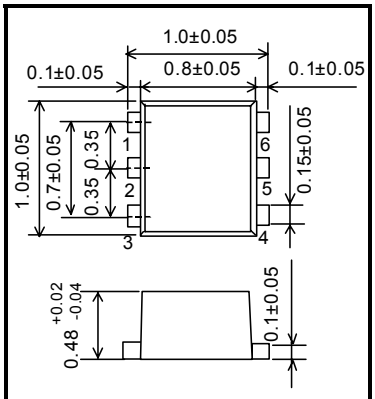


Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−20	V
Collector-emitter voltage	V_{CEO}	−20	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−50	mA
Collector power dissipation	P_C (Note)	50	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Note: Total rating

Unit: mm



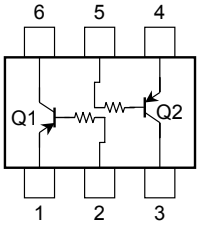
1.EMIITTER1 (E1)
2.BASE1 (B1)
3.COLLECTOR2 (C2)
4.EMITTER2 (E2)
5.BASE2 (B2)
6.COLLECTOR1 (C1)

fS6

JEDEC	—
JEITA	—
TOSHIBA	2-1F1D

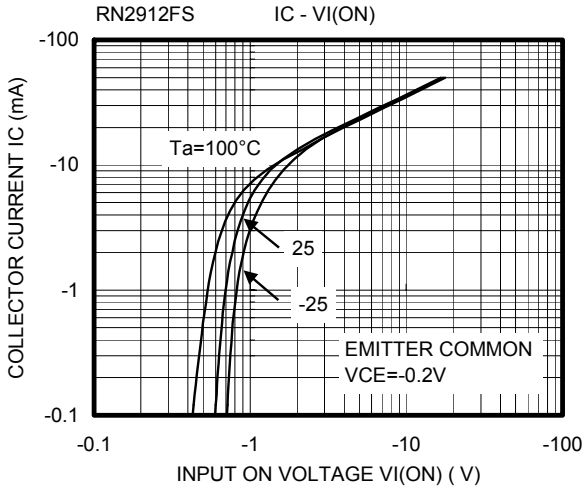
Weight:0.001g (typ.)

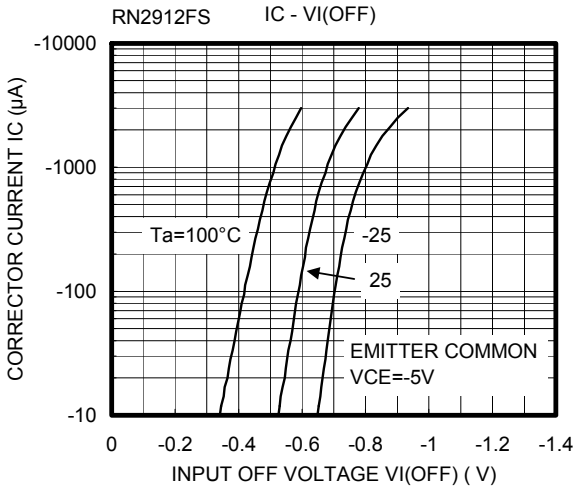
Equivalent Circuit (top view)

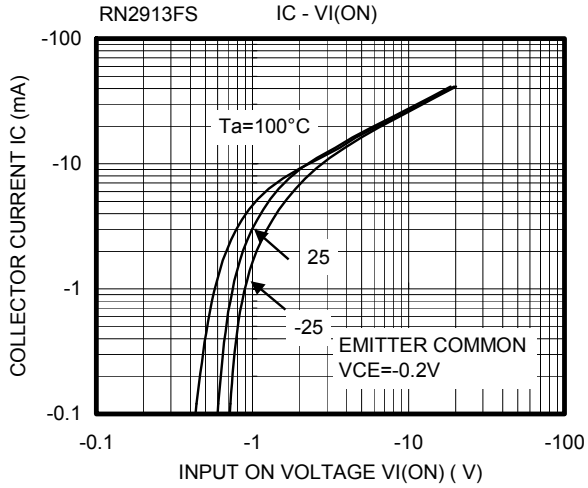


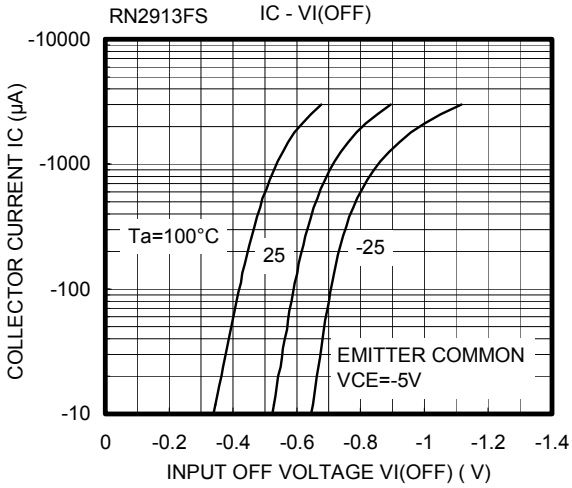
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

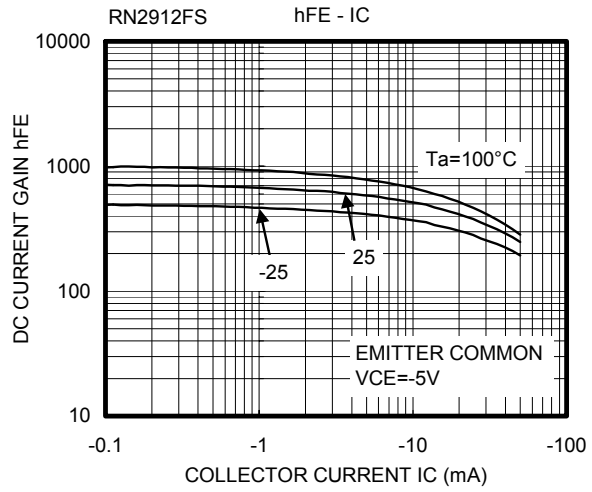
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = −20 V, I_E = 0	—	—	−100	nA
Emitter cut-off current		I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−100	nA
DC current gain		h_{FE}	V_{CE} = −5 V, I_C = −1 mA	300	—	—	
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = −5 mA, I_B = −0.25 mA	—		−0.15	V
Collector output capacitance		C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	1.2	—	pF
Input resistor	RN2912FS	R1	—	17.6	22	26.4	kΩ
	RN2913FS			37.6	47	56.4	

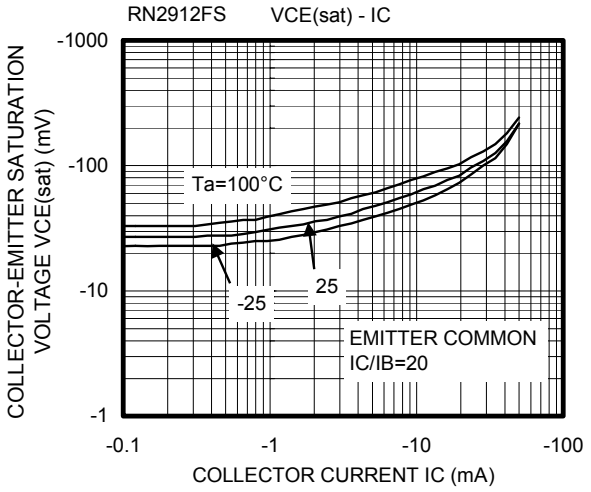

RN2912FS IC - VI(ON)
COLLECTOR CURRENT IC (mA)
-100
-10
-1
-0.1
Ta=100°C
25
-25
EMITTER COMMON
VCE=-0.2V
-0.1
-1
-10
-100
INPUT ON VOLTAGE VI(ON) (V)

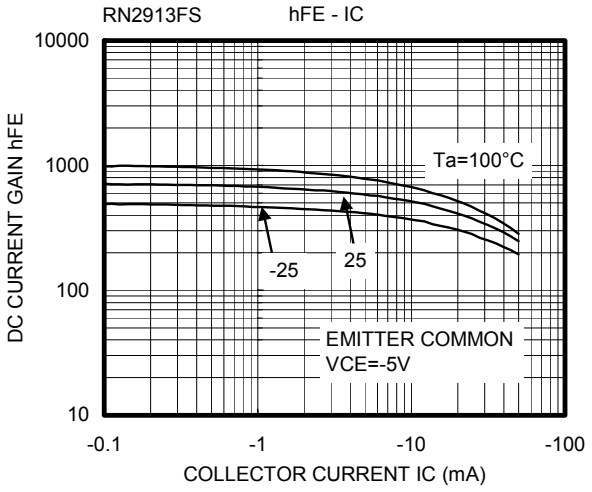

RN2912FS IC - VI(OFF)
CORRECTOR CURRENT IC (µA)
-10000
-1000
-100
-10
Ta=100°C
-25
25
EMITTER COMMON
VCE=-5V
0
-0.2
-0.4
-0.6
-0.8
-1
-1.2
-1.4
INPUT OFF VOLTAGE VI(OFF) (V)

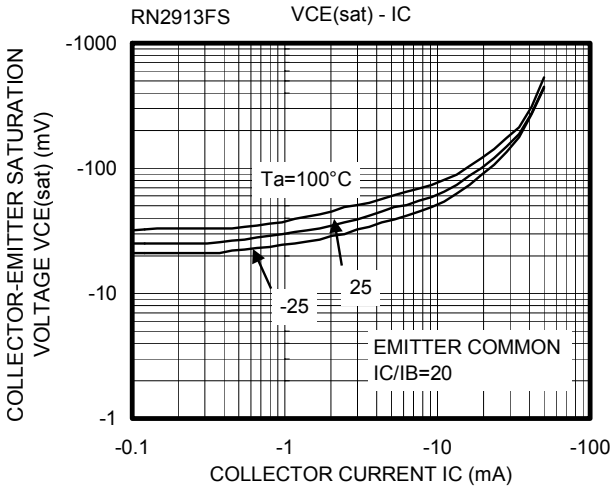

RN2913FS IC - VI(ON)
COLLECTOR CURRENT IC (mA)
-100
-10
-1
-0.1
Ta=100°C
25
-25
EMITTER COMMON
VCE=-0.2V
-0.1
-1
-10
-100
INPUT ON VOLTAGE VI(ON) (V)

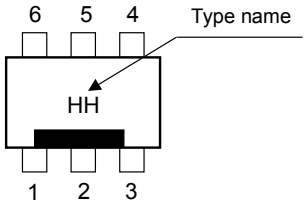
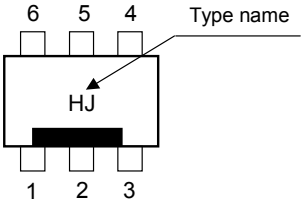

RN2913FS IC - VI(OFF)
COLLECTOR CURRENT IC (µA)
-10000
-1000
-100
-10
Ta=100°C
25
-25
EMITTER COMMON
VCE=-5V
0
-0.2
-0.4
-0.6
-0.8
-1
-1.2
-1.4
INPUT OFF VOLTAGE VI(OFF) (V)


RN2912FS hFE - IC
DC CURRENT GAIN hFE
10000
1000
100
10
Ta=100°C
25
-25
EMITTER COMMON
VCE=-5V
-0.1
-1
-10
-100
COLLECTOR CURRENT IC (mA)


RN2912FS VCE(sat) - IC
COLLECTOR-EMITTER SATURATION VOLTAGE VCE(sat) (mV)
-1000
-100
-10
-1
Ta=100°C
25
-25
EMITTER COMMON
IC/IB=20
-0.1
-1
-10
-100
COLLECTOR CURRENT IC (mA)


RN2913FS hFE - IC
DC CURRENT GAIN hFE
10000
1000
100
10
Ta=100°C
25
-25
EMITTER COMMON
VCE=-5V
-0.1
-1
-10
-100
COLLECTOR CURRENT IC (mA)


RN2913FS VCE(sat) - IC
COLLECTOR-EMITTER SATURATION VOLTAGE VCE(sat) (mV)
-1000
-100
-10
-1
Ta=100°C
25
-25
EMITTER COMMON
IC/IB=20
-0.1
-1
-10
-100
COLLECTOR CURRENT IC (mA)

Type Name	Marking
RN2912FS	
RN2913FS	

HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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